Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK210

FM Tuner Applications VHF Band Amplifier Applications

- High power gain: GPS = 24dB (typ.) (f = 100 MHz)
- Low noise figure: NF = 1.8dB (typ.) (f = 100 MHz)
- High forward transfer admittance: $|Y_{fs}| = 7 \text{ mS (typ.)}$ (f = 1 kHz)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDO}	-18	V
Gate current	IG	10	mA
Drain power dissipation	P _D	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	−55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

2.5 - 0.3

1.5 - 0.15

1.5 - 0.15

2.5 - 0.3

1.5 - 0.15

1.0 - 10

1. DRAIN
2. GATE
3. SOURCE

JEDEC

JEITA

SC-59

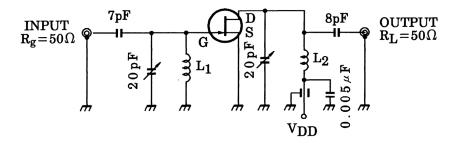
TOSHIBA
2-3F1C

Weight: 0.012 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = -1.0 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	-10	nA
Gate-drain breakdown voltage	V (BR) GDO	$I_G = -100 \mu A$	-18	_	_	V
Drain current	I _{DSS} (Note)	V _{GS} = 0 V, V _{DS} = 10 V	3	_	24	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = 10 \text{ V}, I_D = 1 \mu\text{A}$	-1.2	-3	_	٧
Forward transfer admittance	Y _{fs}	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 kHz	_	7	_	mS
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	3.5	_	pF
Reverse transfer capacitance	C _{rss}	V _{GD} = -10 V, f = 1 MHz	_	_	0.65	pF
Power gain	G _{PS}	V _{DD} = 10 V, f = 100 MHz (Figure 1)	_	24	_	dB
Noise figure	NF	V _{DD} = 10 V, f = 100 MHz (Figure 1)	_	1.8	3.5	dB

Note: I_{DSS} classificatopn Y: 3.0~7.0 mA, GR (R): 6.0~14.0 mA, BL (L): 12.0~24.0 mA

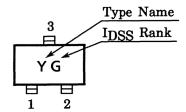


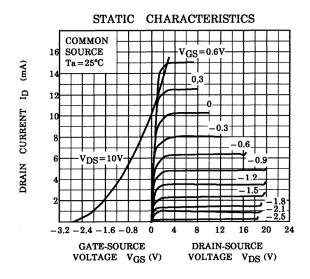
 $L_1{:}~0.8~mm\varphi~A_g$ plated Cu wire 3 turns, 10 mm ID, 10 mm length

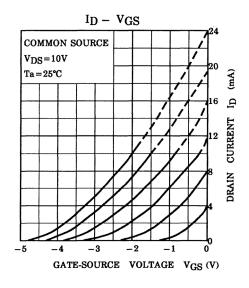
 $L_2{:}~0.8~mm\varphi~A_g~plated~Cu~wire~3.5~turns,~10~mm~ID,~10~mm~length$

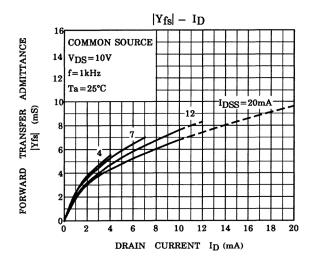
Figure 1 100 MHz G_{ps} NF Test Circuit

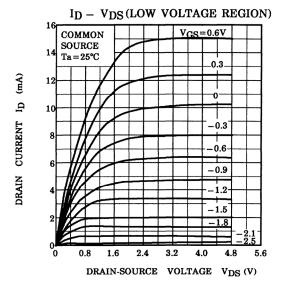
Marking

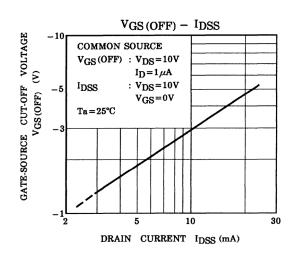


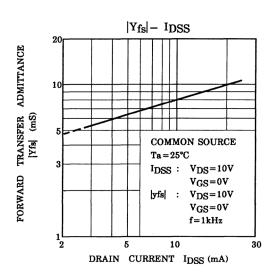




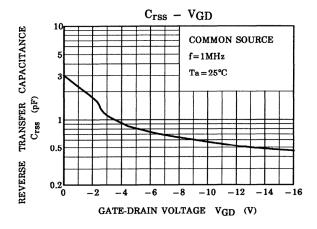


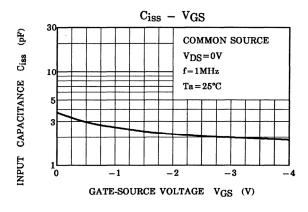


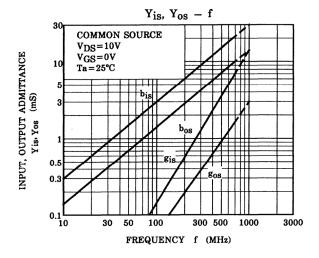


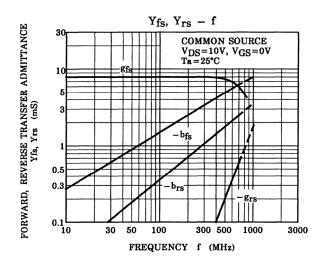


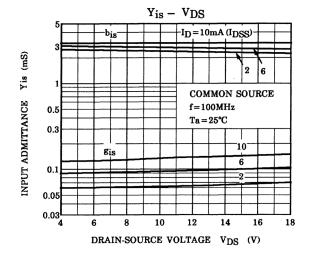
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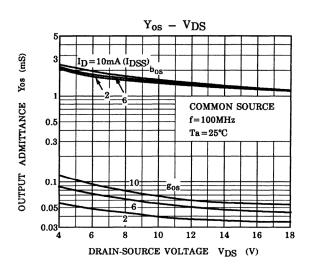


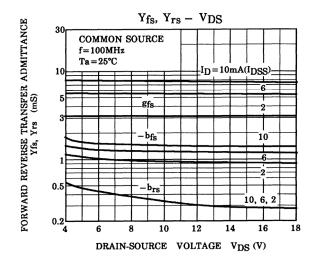


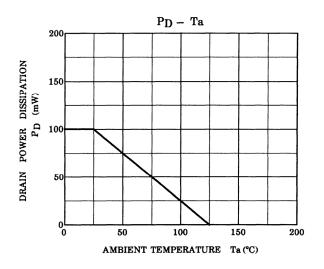












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20070701-EN GENERAL

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